74AVC2T45-Q100

Dual-bit, dual-supply voltage level translator/transceiver; 3-state

Rev. 2 — 15 February 2013

Product data sheet

1. General description

The 74AVC2T45-Q100 is a dual-bit, dual-supply transceiver that enables bidirectional level translation. It features two data input-output ports (nA and nB), a direction control input (DIR) and dual supply pins ($V_{CC(A)}$ and $V_{CC(B)}$). Both $V_{CC(A)}$ and $V_{CC(B)}$ can be supplied with any voltage between 0.8 V and 3.6 V. This flexibility makes the device suitable for translating between any of the low voltage nodes (0.8 V, 1.2 V, 1.5 V, 1.8 V, 2.5 V and 3.3 V). Pins nA and DIR are referenced to $V_{CC(B)}$ and pins nB are referenced to $V_{CC(B)}$. A HIGH on DIR allows transmission from nA to nB and a LOW on DIR allows transmission from nB to nA.

The device is fully specified for partial power-down applications using I_{OFF} . The I_{OFF} circuitry disables the output, preventing any damaging backflow current through the device when it is powered down. In Suspend mode when either $V_{CC(A)}$ or $V_{CC(B)}$ are at GND level, both A and B are in the high-impedance OFF-state.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
 - ◆ Specified from -40 °C to +85 °C and from -40 °C to +125 °C
- Wide supply voltage range:
 - ♦ V_{CC(A)}: 0.8 V to 3.6 V
 - V_{CC(B)}: 0.8 V to 3.6 V
- High noise immunity
- Complies with JEDEC standards:
 - JESD8-12 (0.8 V to 1.3 V)
 - ◆ JESD8-11 (0.9 V to 1.65 V)
 - ◆ JESD8-7 (1.2 V to 1.95 V)
 - ◆ JESD8-5 (1.8 V to 2.7 V)
 - ◆ JESD8-B (2.7 V to 3.6 V)
- ESD protection:
 - MIL-STD-883, method 3015 Class 3B exceeds 8000 V
 - HBM JESD22-A114E Class 3B exceeds 8000 V
 - ♦ MM JESD22-A115-A exceeds 200 V (C = 200 pF, R = 0 Ω)



- Maximum data rates:
 - ◆ 500 Mbit/s (1.8 V to 3.3 V translation)
 - ◆ 320 Mbit/s (<1.8 V to 3.3 V translation)
 - ◆ 320 Mbit/s (translate to 2.5 V or 1.8 V)
 - ◆ 280 Mbit/s (translate to 1.5 V)
 - ◆ 240 Mbit/s (translate to 1.2 V)
- Suspend mode
- Latch-up performance exceeds 100 mA per JESD 78 Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of V_{CC}
- I_{OFF} circuitry provides partial Power-down mode operation
- Multiple package options

3. Ordering information

Table 1. Ordering information

Type number	Package						
	Temperature range	Name	Description	Version			
74AVC2T45DP-Q100	–40 °C to +125 °C	TSSOP8	plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm	SOT505-2			
74AVC2T45DC-Q100	–40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1			
74AVC2T45GD-Q100	–40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body $3 \times 2 \times 0.5$ mm	SOT996-2			

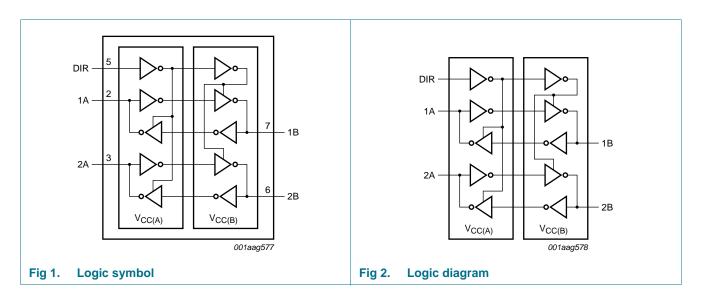
4. Marking

Table 2. Marking

Type number	Marking code ^[1]
74AVC2T45DP-Q100	B45
74AVC2T45DC-Q100	B45
74AVC2T45GD-Q100	B45

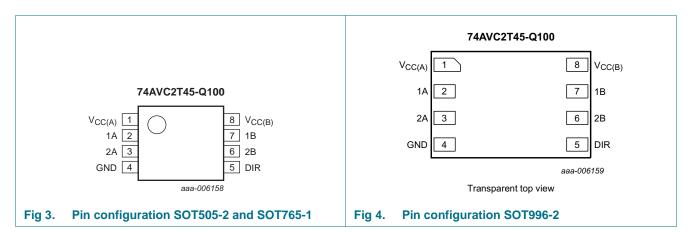
^[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram



6. Pinning information

6.1 Pinning



6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
$V_{CC(A)}$	1	supply voltage A (referenced to pins 1A, 2A and DIR)
1A	2	data input or output
2A	3	data input or output
GND	4	ground (0 V)
DIR	5	direction control
2B	6	data input or output
1B	7	data input or output
V _{CC(B)}	8	supply voltage B (referenced to pins 1B and 2B)

7. Functional description

Table 4. Function table[1]

Supply voltage	Input	Input/output ^[2]			
V _{CC(A)} , V _{CC(B)}	DIR[3]	nA nB			
0.8 V to 3.6 V	L	nA = nB	input		
0.8 V to 3.6 V	Н	input	nB = nA		
GND[4]	X	Z	Z		

^[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

^[2] The input circuit of the data I/O is always active.

^[3] The DIR input circuit is referenced to $V_{CC(A)}$.

^[4] If at least one of $V_{\text{CC(A)}}$ or $V_{\text{CC(B)}}$ is at GND level, the device goes into Suspend mode.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC(A)}$	supply voltage A		-0.5	+4.6	V
$V_{CC(B)}$	supply voltage B		-0.5	+4.6	V
I _{IK}	input clamping current	V _I < 0 V	-50	-	mA
VI	input voltage		<u>[1]</u> –0.5	+4.6	V
I _{OK}	output clamping current	V _O < 0 V	-50	-	mA
Vo	output voltage	Active mode	[1][2][3] -0.5	$V_{CCO} + 0.5$	V
		Suspend or 3-state mode	<u>[1]</u> –0.5	+4.6	V
Io	output current	$V_O = 0 V \text{ to } V_{CCO}$	-	±50	mA
I _{CC}	supply current	$I_{CC(A)}$ or $I_{CC(B)}$	-	100	mA
I_{GND}	ground current		-100	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +125 ^{\circ}\text{C}$	<u>[4]</u> _	250	mW

^[1] The minimum input voltage rating and output voltage ratings may be exceeded if the input and output current ratings are observed.

9. Recommended operating conditions

Table 6. Recommended operating conditions

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Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC(A)}$	supply voltage A		0.8	3.6	V
$V_{CC(B)}$	supply voltage B		0.8	3.6	V
VI	input voltage		0	3.6	V
Vo	output voltage	Active mode	<u>[1]</u> 0	V _{cco}	V
		Suspend or 3-state mode	0	3.6	V
T _{amb}	ambient temperature		-40	+125	°C
Δt/ΔV	input transition rise and fall rate	$V_{CCI} = 0.8 \text{ V to } 3.6 \text{ V}$	<u>[2]</u> -	5	ns/V

^[1] V_{CCO} is the supply voltage associated with the output port.

^[2] V_{CCO} is the supply voltage associated with the output port.

^[3] V_{CCO} + 0.5 V should not exceed 4.6 V.

^[4] For TSSOP8 package: above 55 °C the value of P_{tot} derates linearly at 2.5 mW/K. For VSSOP8 package: above 110 °C the value of P_{tot} derates linearly with 8 mW/K. For XSON8 package: above 118 °C the value of P_{tot} derates linearly with 7.8 mW/K.

^[2] V_{CCI} is the supply voltage associated with the input port.

10. Static characteristics

Table 7. Typical static characteristics at $T_{amb} = 25 \, {}^{\circ}C_{1}^{1}$

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_{O} = -1.5 \text{ mA}; V_{CC(A)} = V_{CC(B)} = 0.8 \text{ V}$	-	0.69	-	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_{O} = 1.5 \text{ mA}; V_{CC(A)} = V_{CC(B)} = 0.8 \text{ V}$	-	0.07	-	V
l _l	input leakage current	DIR input; $V_1 = 0 \text{ V or } 3.6 \text{ V}$; $V_{CC(A)} = V_{CC(B)} = 0.8 \text{ V to } 3.6 \text{ V}$	-	±0.025	±0.25	μΑ
I _{OZ}	OFF-state output current	A or B port; $V_O = 0$ V or V_{CCO} ; $V_{CC(A)} = V_{CC(B)} = 0.8$ V to 3.6 V	<u>[3]</u> _	±0.5	±2.5	μΑ
l _{OFF}	power-off leakage current	A port; V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC(A)} = 0$ V; $V_{CC(B)} = 0.8$ V to 3.6 V	-	±0.1	±1	μΑ
		B port; V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC(B)} = 0$ V; $V_{CC(A)} = 0.8$ V to 3.6 V	-	±0.1	±1	μΑ
C _I	input capacitance	DIR input; $V_1 = 0 \text{ V or } 3.3 \text{ V}$; $V_{CC(A)} = V_{CC(B)} = 3.3 \text{ V}$	-	1.0	-	pF
C _{I/O}	input/output capacitance	A and B port; Suspend mode; $V_O = V_{CCO}$ or GND; $V_{CC(A)} = V_{CC(B)} = 3.3 \text{ V}$	-	4.0	-	pF

^[1] V_{CCO} is the supply voltage associated with the output port.

Table 8. Static characteristics [1][2]

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	-40 °C to	+85 °C	-40 °C to	-40 °C to +125 °C		
			Min	Max	Min	Max		
V_{IH}	V _{IH} HIGH-level input voltage	data input						
in		$V_{CCI} = 0.8 \text{ V}$	0.70V _{CCI}	-	0.70V _{CCI}	-	V	
		$V_{CCI} = 1.1 \text{ V to } 1.95 \text{ V}$	$0.65V_{CCI}$	-	$0.65V_{CCI}$	-	V	
		V_{CCI} = 2.3 V to 2.7 V	1.6	-	1.6	-	V	
		$V_{CCI} = 3.0 \text{ V to } 3.6 \text{ V}$	2	-	2	-	V	
		DIR input						
		$V_{CC(A)} = 0.8 \text{ V}$	$0.70V_{CC(A)}$	-	$0.70V_{CC(A)}$	-	V	
		$V_{CC(A)} = 1.1 \text{ V to } 1.95 \text{ V}$	0.65V _{CC(A)}	-	$0.65V_{CC(A)}$	-	V	
		$V_{CC(A)} = 2.3 \text{ V to } 2.7 \text{ V}$	1.6	-	1.6	-	V	
		$V_{CC(A)} = 3.0 \text{ V to } 3.6 \text{ V}$	2	-	2	-	V	

^[2] V_{CCI} is the supply voltage associated with the data input port.

^[3] For I/O ports, the parameter I_{OZ} includes the input leakage current.

Table 8. Static characteristics ...continued 11[2]
At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	-40 °C t	o +85 °C	-40 °C to	–40 °C to +125 °C			
			Min	Max	Min	Max			
V _{IL}	LOW-level	data input	'		1				
	input voltage	V _{CCI} = 0.8 V	-	0.30V _{CCI}	-	0.30V _{CCI}	V		
		V _{CCI} = 1.1 V to 1.95 V	-	0.35V _{CCI}	-	0.35V _{CCI}	V		
		$V_{CCI} = 2.3 \text{ V to } 2.7 \text{ V}$	-	0.7	-	0.7	V		
		$V_{CCI} = 3.0 \text{ V to } 3.6 \text{ V}$	-	0.9	-	0.9	V		
		DIR input							
		$V_{CC(A)} = 0.8 \text{ V}$	-	0.30V _{CC(A)}	-	0.30V _{CC(A)}	V		
		$V_{CC(A)} = 1.1 \text{ V to } 1.95 \text{ V}$	-	0.35V _{CC(A)}	-	0.35V _{CC(A)}	V		
		$V_{CC(A)} = 2.3 \text{ V to } 2.7 \text{ V}$	-	0.7	-	0.7	V		
		$V_{CC(A)} = 3.0 \text{ V to } 3.6 \text{ V}$	-	0.9	-	0.9	V		
√ _{он}	HIGH-level	$V_I = V_{IH}$ or V_{IL}							
	output voltage	$I_O = -100 \mu A;$ $V_{CC(A)} = V_{CC(B)} = 0.8 \text{ V to } 3.6 \text{ V}$	V _{CCO} - 0.1	-	V _{CCO} - 0.1	-	V		
		$I_O = -3 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 1.1 \text{ V}$	0.85	-	0.85	-	V		
		$I_O = -6 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 1.4 \text{ V}$	1.05	-	1.05	-	V		
		$I_{O} = -8 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 1.65 \text{ V}$	1.2	-	1.2	-	V		
		$I_O = -9 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 2.3 \text{ V}$	1.75	-	1.75	-	V		
		$I_O = -12 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 3.0 \text{ V}$	2.3	-	2.3	-	V		
OL	LOW-level	$V_I = V_{IH}$ or V_{IL}							
	output voltage	$I_{O} = 100 \ \mu A;$ $V_{CC(A)} = V_{CC(B)} = 0.8 \ V \ to \ 3.6 \ V$	-	0.1	-	0.1	V		
		$I_O = 3 \text{ mA}; V_{CC(A)} = V_{CC(B)} = 1.1 \text{ V}$	-	0.25	-	0.25	V		
		$I_O = 6 \text{ mA}; V_{CC(A)} = V_{CC(B)} = 1.4 \text{ V}$	-	0.35	-	0.35	V		
		$I_O = 8 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 1.65 \text{ V}$	-	0.45	-	0.45	V		
		$I_O = 9 \text{ mA}; V_{CC(A)} = V_{CC(B)} = 2.3 \text{ V}$	-	0.55	-	0.55	V		
		$I_O = 12 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 3.0 \text{ V}$	-	0.7	-	0.7	V		
	input leakage current	DIR input; $V_I = 0 \text{ V or } 3.6 \text{ V};$ $V_{CC(A)} = V_{CC(B)} = 0.8 \text{ V to } 3.6 \text{ V}$	-	±1	-	±1.5	μΑ		
OZ	OFF-state output current	A or B port; $V_O = 0 \text{ V or } V_{CCO}$; $V_{CC(A)} = V_{CC(B)} = 3.6 \text{ V}$	[3] -	±5	-	±7.5	μΑ		
OFF	power-off leakage	A port; V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC(A)} = 0$ V; $V_{CC(B)} = 0.8$ V to 3.6 V	-	±5	-	±35	μΑ		
	current	B port; V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC(B)} = 0$ V; $V_{CC(A)} = 0.8$ V to 3.6 V	-	±5	-	±35	μΑ		

Table 8. Static characteristics ...continued[1][2]

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	–40 °C t	o +85 °C	-40 °C to +125 °C		Unit	
			Min	Max	Min	Max		
I_{CC}	supply current	A port; $V_I = 0 \text{ V or } V_{CCI}$; $I_O = 0 \text{ A}$				•	'	
			$V_{CC(A)} = 0.8 \text{ V to } 3.6 \text{ V};$ $V_{CC(B)} = 0.8 \text{ V to } 3.6 \text{ V}$	-	8	-	11.5	μΑ
		$V_{CC(A)} = 3.6 \text{ V}; V_{CC(B)} = 0 \text{ V}$	-	8	-	11.5	μΑ	
		$V_{CC(A)} = 0 \text{ V}; V_{CC(B)} = 3.6 \text{ V}$	-2	-	-8	-	μА	
		B port; $V_I = 0 \text{ V or } V_{CCI}$; $I_O = 0 \text{ A}$						
		$V_{CC(A)} = 0.8 \text{ V to } 3.6 \text{ V};$ $V_{CC(B)} = 0.8 \text{ V to } 3.6 \text{ V}$	-	8	-	11.5	μΑ	
		$V_{CC(A)} = 3.6 \text{ V}; V_{CC(B)} = 0 \text{ V}$	-2	-	-8	-	μΑ	
		$V_{CC(A)} = 0 \text{ V}; V_{CC(B)} = 3.6 \text{ V}$	-	8	-	11.5	μΑ	
		A plus B port ($I_{CC(A)} + I_{CC(B)}$); $I_O = 0$ A; $V_I = 0$ V or V_{CCI} ; $V_{CC(A)} = 0.8$ V to 3.6 V; $V_{CC(B)} = 0.8$ V to 3.6 V	-	16	-	23	μА	

^[1] V_{CCO} is the supply voltage associated with the output port.

^[2] V_{CCI} is the supply voltage associated with the data input port.

^[3] For I/O ports, the parameter I_{OZ} includes the input leakage current.

11. Dynamic characteristics

Table 9. Typical dynamic characteristics at $V_{CC(A)} = 0.8 \text{ V}$ and $T_{amb} = 25 ^{\circ}\text{C}$ [1]

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 7; for wave forms see Figure 5 and Figure 6

•									•.
Symbol	Parameter	Conditions			V _C	C(B)			Unit
			0.8 V	1.2 V	1.5 V	1.8 V	2.5 V	3.3 V	
t_{pd}	propagation delay	A to B	15.5	8.1	7.6	7.7	8.4	9.2	ns
		B to A	15.5	12.7	12.3	12.2	12.0	11.8	ns
t _{dis}	disable time	DIR to A	12.2	12.2	12.2	12.2	12.2	12.2	ns
		DIR to B	11.7	7.9	7.6	8.2	8.7	10.2	ns
t _{en}	t _{en} enable time	DIR to A	27.2	20.6	19.9	20.4	20.7	22.0	ns
		DIR to B	27.7	20.3	19.8	19.9	20.6	21.4	ns

^[1] t_{pd} is the same as t_{PLH} and t_{PHL}; t_{dis} is the same as t_{PLZ} and t_{PHZ}; t_{en} is the same as t_{PZL} and t_{PZH}. t_{en} is a calculated value using the formula shown in Section 13.4 "Enable times"

Table 10. Typical dynamic characteristics at $V_{CC(B)} = 0.8 \text{ V}$ and $T_{amb} = 25 ^{\circ}\text{C}$ [1]

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 7; for wave forms see Figure 5 and Figure 6

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Symbol	Parameter	V _{CC(A)}						Unit	
			0.8 V	1.2 V	1.5 V	1.8 V	2.5 V	3.3 V	
t_{pd}	propagation delay	A to B	15.5	12.7	12.3	12.2	12.0	11.8	ns
		B to A	15.5	8.1	7.6	7.7	8.4	9.2	ns
t _{dis}	disable time	DIR to A	12.2	4.9	3.8	3.7	2.8	3.4	ns
		DIR to B	11.7	9.2	9.0	8.8	8.7	8.6	ns
t _{en}	enable time	DIR to A	27.2	17.3	16.6	16.5	17.1	17.8	ns
		DIR to B	27.7	17.6	16.1	15.9	14.8	15.2	ns

^[1] t_{pd} is the same as t_{PLH} and t_{PHL}; t_{dis} is the same as t_{PLZ} and t_{PHZ}; t_{en} is the same as t_{PZL} and t_{PZH}.
t_{en} is a calculated value using the formula shown in Section 13.4 "Enable times"

Table 11. Typical power dissipation capacitance at $V_{CC(A)} = V_{CC(B)}$ and $T_{amb} = 25 \, ^{\circ}C$ [1][2]

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions			V _{CC(A)} ar	nd V _{CC(B)}			Unit
			0.8 V	1.2 V	1.5 V	1.8 V	2.5 V	3.3 V	
C_{PD}	power dissipation capacitance	A port: (direction A to B); B port: (direction B to A)	1	2	2	2	2	2	pF
		A port: (direction B to A); B port: (direction A to B)	9	11	11	12	14	17	pF

^[1] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

 $P_D = C_{PD} \times V_{CC}{}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}{}^2 \times f_o) \text{ where:}$

f_i = input frequency in MHz;

fo = output frequency in MHz;

C_L = load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

[2] f_i = 10 MHz; V_I = GND to V_{CC} ; t_r = t_f = 1 ns; C_L = 0 pF; R_L = ∞ Ω .

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Table 12. Dynamic characteristics for temperature range –40 °C to +85 °C [1]

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 7; for wave forms see Figure 5 and Figure 6.

Symbol	Parameter	Conditions	V _{CC(B)}		4 F V	+04V	101/	0.45 \/	25.7	± 0.2 V	221	L 0 2 V	Unit
				± 0.1 V		± 0.1 V		0.15 V				± 0.3 V	_
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
	1.1 V to 1.3 V												
t _{pd}	propagation	A to B	1.0	9.0	0.7	6.8	0.6	6.1	0.5	5.7	0.5	6.1	ns
	delay	B to A	1.0	9.0	0.8	8.0	0.7	7.7	0.6	7.2	0.5	7.1	ns
t_{dis}	disable time	DIR to A	2.2	8.8	2.2	8.8	2.2	8.8	2.2	8.8	2.2	8.8	ns
		DIR to B	2.2	8.4	1.8	6.7	2.0	6.9	1.7	6.2	2.4	7.2	ns
t _{en}	enable time	DIR to A	-	17.4	-	14.7	-	14.6	-	13.4	-	14.3	ns
		DIR to B	-	17.8	-	15.6	-	14.9	-	14.5	-	14.9	ns
$V_{CC(A)} =$	1.4 V to 1.6 V												
t _{pd}	propagation	A to B	1.0	8.0	0.7	5.4	0.6	4.6	0.5	3.7	0.5	3.5	ns
	delay	B to A	1.0	6.8	0.8	5.4	0.7	5.1	0.6	4.7	0.5	4.5	ns
t _{dis}	disable time	DIR to A	1.6	6.3	1.6	6.3	1.6	6.3	1.6	6.3	1.6	6.3	ns
		DIR to B	2.0	7.6	1.8	5.9	1.6	6.0	1.2	4.8	1.7	5.5	ns
t _{en}	enable time	DIR to A	-	14.4	-	11.3	-	11.1	-	9.5	-	10.0	ns
		DIR to B	-	14.3	-	11.7	-	10.9	-	10.0	-	9.8	ns
V _{CC(A)} =	1.65 V to 1.95	V											
t _{pd} propagation		A to B	1.0	7.7	0.6	5.1	0.5	4.3	0.5	3.4	0.5	3.1	ns
	delay	B to A	1.0	6.1	0.7	4.6	0.5	4.4	0.5	3.9	0.5	3.7	ns
t _{dis}	disable time	DIR to A	1.6	5.5	1.6	5.5	1.6	5.5	1.6	5.5	1.6	5.5	ns
		DIR to B	1.8	7.7	1.8	5.7	1.4	5.8	1.0	4.5	1.5	5.2	ns
t _{en}	enable time	DIR to A	-	13.8	-	10.3	-	10.2	-	8.4	-	8.9	ns
		DIR to B	-	13.2	-	10.6	-	9.8	-	8.9	-	8.6	ns
V _{CC(A)} =	2.3 V to 2.7 V												
t _{pd}	propagation	A to B	1.0	7.2	0.5	4.7	0.5	3.9	0.5	3.0	0.5	2.6	ns
	delay	B to A	1.0	5.7	0.6	3.8	0.5	3.4	0.5	3.0	0.5	2.8	ns
t _{dis}	disable time	DIR to A	1.5	4.2	1.5	4.2	1.5	4.2	1.5	4.2	1.5	4.2	ns
		DIR to B	1.7	7.3	2.0	5.2	1.5	5.1	0.6	4.2	1.1	4.8	ns
t _{en}	enable time	DIR to A	-	13.0	-	9.0	-	8.5	-	7.2	-	7.6	ns
		DIR to B	-	11.4	-	8.9	-	8.1	-	7.2	-	6.8	ns
V _{CC(A)} =	3.0 V to 3.6 V												
t _{pd}	propagation	A to B	1.0	7.1	0.5	4.5	0.5	3.7	0.5	2.8	0.5	2.4	ns
	delay	B to A	1.0	6.1	0.6	3.6	0.5	3.1	0.5	2.6	0.5	2.4	ns
t _{dis}	disable time	DIR to A	1.5	4.7	1.5	4.7	1.5	4.7	1.5	4.7	1.5	4.7	ns
		DIR to B	1.7	7.2	0.7	5.5	0.6	5.5	0.7	4.1	1.7	4.7	ns
t _{en}	enable time	DIR to A	-	13.3	-	9.1	-	8.6	-	6.7	-	7.1	ns
-611		DIR to B	-	11.8	-	9.2	-	8.4	-	7.5	-	7.1	ns

^[1] t_{pd} is the same as t_{PLH} and t_{PHL} ; t_{dis} is the same as t_{PLZ} and t_{PHZ} ; t_{en} is the same as t_{PZL} and t_{PZH} .

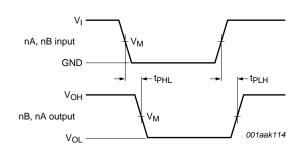
Table 13. Dynamic characteristics for temperature range –40 °C to +125 °C [1]

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 7; for wave forms see Figure 5 and Figure 6

Symbol	Parameter	Conditions	V _{CC(B)}	± 0.1 V	15 V	± 0.1 V	1 8 V -	± 0.15 V	25 V	± 0.2 V	33V.	± 0.3 V	Uni
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
Vcc(A) =	1.1 V to 1.3 V			Мах	10000	Ших		max		шах		Мах	
t _{pd}	propagation	A to B	1.0	9.9	0.7	7.5	0.6	6.8	0.5	6.3	0.5	6.8	ns
•ра	delay	B to A	1.0	9.9	0.8	8.8	0.7	8.5	0.6	8.0	0.5	7.9	ns
t _{dis}	disable time	DIR to A	2.2	9.7	2.2	9.7	2.2	9.7	2.2	9.7	2.2	9.7	ns
uis	aloable time	DIR to B	2.2	9.2	1.8	7.4	2.0	7.6	1.7	6.9	2.4	8.0	ns
t _{en}	enable time	DIR to A		19.1	-	16.2	-	16.1	-	14.9		15.9	ns
·en		DIR to B	_	19.6	-	17.2	-	16.5	_	16.0	_	16.5	ns
Vcc(A) =	1.4 V to 1.6 V	2											
t _{pd}	propagation	A to B	1.0	8.8	0.7	6.0	0.6	5.1	0.5	4.1	0.5	3.9	ns
·pu	delay	B to A	1.0	7.5	0.8	6.0	0.7	5.7	0.6	5.2	0.5	5.0	ns
t _{dis}	disable time	DIR to A	1.6	7.0	1.6	7.0	1.6	7.0	1.6	7.0	1.6	7.0	ns
uio		DIR to B	2.0	8.3	1.8	6.5	1.6	6.6	1.2	5.3	1.7	6.1	ns
t _{en}	enable time	DIR to A	-	15.8	-	12.5	-	12.3	-	10.5	-	11.1	ns
011		DIR to B	-	15.8	-	13.0	-	12.1	-	11.1	-	10.9	ns
V _{CC(A)} =	1.65 V to 1.95												
t _{pd}	propagation	A to B	1.0	8.5	0.6	5.7	0.5	4.8	0.5	3.8	0.5	3.5	ns
	delay	B to A	1.0	6.8	0.7	5.1	0.5	4.9	0.5	4.3	0.5	4.1	ns
t _{dis}	disable time	DIR to A	1.6	6.1	1.6	6.1	1.6	6.1	1.6	6.1	1.6	6.1	ns
		DIR to B	1.8	8.5	1.8	6.3	1.4	6.4	1.0	5.0	1.5	5.8	ns
t _{en}	enable time	DIR to A	-	15.3	-	11.4	-	11.3	-	9.3	-	9.9	ns
		DIR to B	-	14.6	-	11.8	-	10.9	-	9.9	-	9.6	ns
V _{CC(A)} =	2.3 V to 2.7 V												
t _{pd}	propagation	A to B	1.0	8.0	0.5	5.2	0.5	4.3	0.5	3.3	0.5	2.9	ns
	delay	B to A	1.0	6.3	0.6	4.2	0.5	3.8	0.5	3.3	0.5	3.1	ns
t _{dis}	disable time	DIR to A	1.5	4.7	1.5	4.7	1.5	4.7	1.5	4.7	1.5	4.7	ns
		DIR to B	1.7	8.0	2.0	5.8	1.5	5.7	0.6	4.7	1.1	5.3	ns
t _{en}	enable time	DIR to A	-	14.3	-	10.0	-	9.5	-	8.0	-	8.4	ns
		DIR to B	-	12.7	-	9.9	-	9.0	-	8.0	-	7.6	ns
V _{CC(A)} =	3.0 V to 3.6 V												
t _{pd}	propagation	A to B	1.0	7.9	0.5	5.0	0.5	4.1	0.5	3.1	0.5	2.7	ns
	delay	B to A	1.0	6.8	0.6	4.0	0.5	3.5	0.5	2.9	0.5	2.7	ns
t _{dis}	disable time	DIR to A	1.5	5.2	1.5	5.2	1.5	5.2	1.5	5.2	1.5	5.2	ns
		DIR to B	1.7	7.9	0.7	6.1	0.6	6.1	0.7	4.6	1.7	5.2	ns
t _{en}	enable time	DIR to A	-	14.7	-	10.1	-	9.6	-	7.5	-	7.9	ns
		DIR to B	-	13.1	-	10.2	-	9.3	-	8.3	-	7.9	ns

^[1] t_{pd} is the same as t_{PLH} and t_{PHL} ; t_{dis} is the same as t_{PLZ} and t_{PHZ} ; t_{en} is the same as t_{PZL} and t_{PZH} .

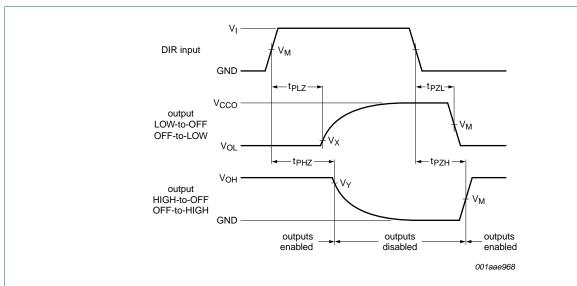
12. Waveforms



Measurement points are given in Table 14.

 $\ensuremath{V_{OL}}$ and $\ensuremath{V_{OH}}$ are typical output voltage levels that occur with the output load.

Fig 5. The data input (nA, nB) to output (nB, nA) propagation delay times



Measurement points are given in Table 14.

V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

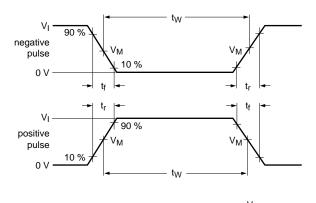
Fig 6. Enable and disable times

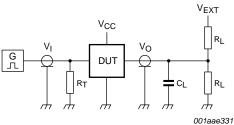
Table 14. Measurement points

Supply voltage	Input ^[1]	Output ^[2]					
V _{CC(A)} , V _{CC(B)}	V _M	V _M	V _X	V _Y			
1.1 V to 1.6 V	0.5V _{CCI}	0.5V _{CCO}	V _{OL} + 0.1 V	V _{OH} – 0.1 V			
1.65 V to 2.7 V	0.5V _{CCI}	0.5V _{CCO}	V _{OL} + 0.15 V	V _{OH} – 0.15 V			
3.0 V to 3.6 V	0.5V _{CCI}	0.5V _{CCO}	V _{OL} + 0.3 V	V _{OH} – 0.3 V			

^[1] V_{CCI} is the supply voltage associated with the data input port.

^[2] V_{CCO} is the supply voltage associated with the output port.





Test data is given in Table 15.

 R_L = Load resistance.

 C_L = Load capacitance including jig and probe capacitance.

 R_T = Termination resistance.

 V_{EXT} = External voltage for measuring switching times.

Fig 7. Test circuit for measuring switching times

Table 15. Test data

Supply voltage	Input		Load		V _{EXT}	V _{EXT}			
V _{CC(A)} , V _{CC(B)}	V _I [1]	Δt/ΔV[2]	CL	R _L	t _{PLH} , t _{PHL}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ} [3]		
1.1 V to 1.6 V	V_{CCI}	≤ 1.0 ns/V	15 pF	2 kΩ	open	GND	2V _{CCO}		
1.65 V to 2.7 V	V_{CCI}	≤ 1.0 ns/V	15 pF	2 kΩ	open	GND	2V _{CCO}		
3.0 V to 3.6 V	V_{CCI}	≤ 1.0 ns/V	15 pF	2 kΩ	open	GND	2V _{CCO}		

[1] V_{CCI} is the supply voltage associated with the data input port.

[2] dV/dt ≥ 1.0 V/ns

[3] V_{CCO} is the supply voltage associated with the output port.

13. Application information

13.1 Unidirectional logic level-shifting application

The circuit given in <u>Figure 8</u> is an example of the 74AVC2T45-Q100 being used in a unidirectional logic level-shifting application.

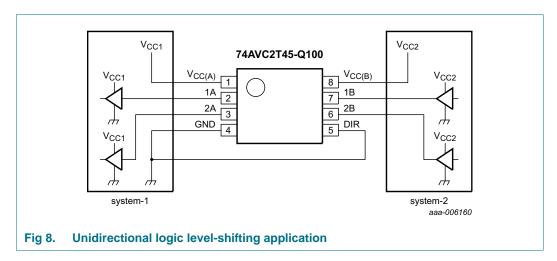


Table 16. Unidirectional logic level-shifting application

Name	Function	Description
$V_{CC(A)}$	V_{CC1}	supply voltage of system-1 (0.8 V to 3.6 V)
1A	OUT1	output level depends on V _{CC1} voltage
2A	OUT2	output level depends on V _{CC1} voltage
GND	GND	device GND
DIR	DIR	the GND (LOW level) determines B port to A port direction
2B	IN2	input threshold value depends on V _{CC2} voltage
1B	IN1	input threshold value depends on V _{CC2} voltage
$V_{CC(B)}$	V_{CC2}	supply voltage of system-2 (0.8 V to 3.6 V)
	V _{CC(A)} 1A 2A GND DIR 2B 1B	V _{CC(A)} V _{CC1} 1A OUT1 2A OUT2 GND GND DIR DIR 2B IN2 1B IN1

13.2 Bidirectional logic level-shifting application

<u>Figure 9</u> shows the 74AVC2T45-Q100 being used in a bidirectional logic level-shifting application. Since the device does not have an output enable (OE) pin, the system designer must take precautions to avoid bus contention between system-1 and system-2 when changing directions.

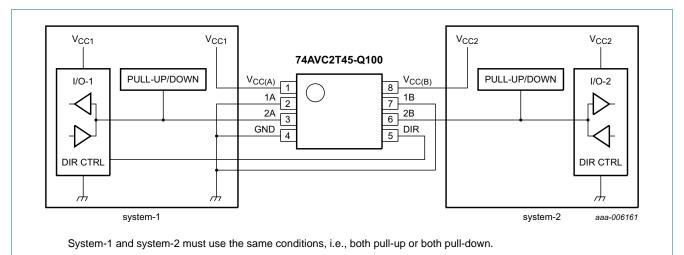


Fig 9. Bidirectional logic level-shifting application

<u>Table 17</u> gives a sequence that illustrates data transmission from system-1 to system-2 and then from system-2 to system-1.

Table 17. Bidirectional logic level-shifting application [1][2]

		_		
State	DIR CTRL	I/O-1	I/O-2	Description
1	Н	output	input	system-1 data to system-2
2	Н	Z	Z	system-2 is getting ready to send data to system-1. I/O-1 and I/O-2 are disabled. The bus-line state depends on the pull-up or pull-down.
3	L	Z	Z	DIR bit is set LOW. I/O-1 and I/O-2 are still disabled. The bus-line state depends on the pull-up or pull-down.
4	L	input	output	system-2 data to system-1

^[1] System-1 and system-2 must use the same conditions, i.e., both pull-up or both pull-down.

^[2] H = HIGH voltage level;

L = LOW voltage level;

Z = high-impedance OFF-state.

13.3 Power-up considerations

The device is designed such that no special power-up sequence is required other than GND being applied first.

Table 18. Typical total supply current $(I_{CC(A)} + I_{CC(B)})$

				. ,	. ,			
V _{CC(A)}	V _{CC(B)}							Unit
	0 V	0.8 V	1.2 V	1.5 V	1.8 V	2.5 V	3.3 V	
0 V	0	0.1	0.1	0.1	0.1	0.1	0.1	μΑ
0.8 V	0.1	0.1	0.1	0.1	0.1	0.7	2.3	μΑ
1.2 V	0.1	0.1	0.1	0.1	0.1	0.3	1.4	μΑ
1.5 V	0.1	0.1	0.1	0.1	0.1	0.1	0.9	μΑ
1.8 V	0.1	0.1	0.1	0.1	0.1	0.1	0.5	μΑ
2.5 V	0.1	0.7	0.3	0.1	0.1	0.1	0.1	μΑ
3.3 V	0.1	2.3	1.4	0.9	0.5	0.1	0.1	μΑ

13.4 Enable times

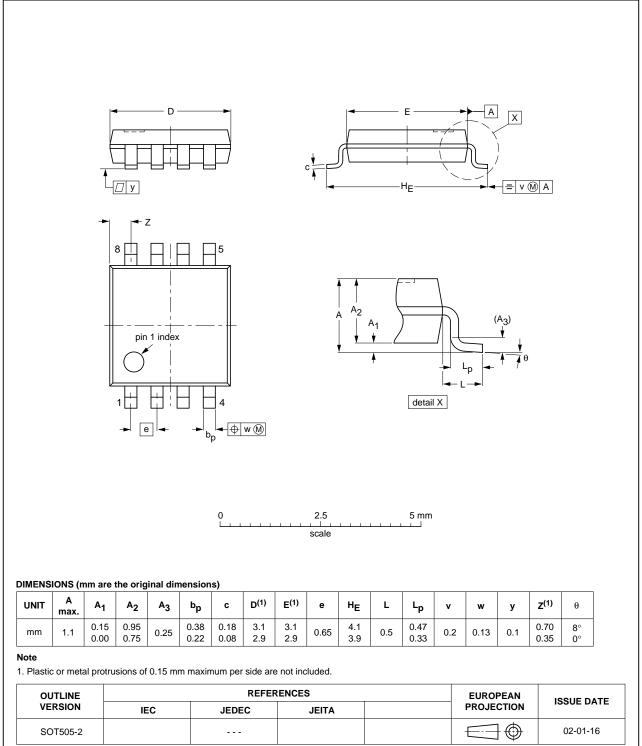
The enable times for the 74AVC2T45-Q100 are calculated from the following formulas:

- t_{en} (DIR to nA) = t_{dis} (DIR to nB) + t_{pd} (nB to nA)
- t_{en} (DIR to nB) = t_{dis} (DIR to nA) + t_{pd} (nA to nB)

In a bidirectional application, these enable times provide the maximum delay from the time the DIR bit is switched until an output is expected. For example, the 74AVC2T45-Q100 is initially transmitting from A to B, then the DIR bit is switched. Disable the B port of the device before presenting it with an input. After the B port has been disabled, an input signal applied to it appears on the corresponding A port after the specified propagation delay.

14. Package outline

TSSOP8: plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm SOT505-2



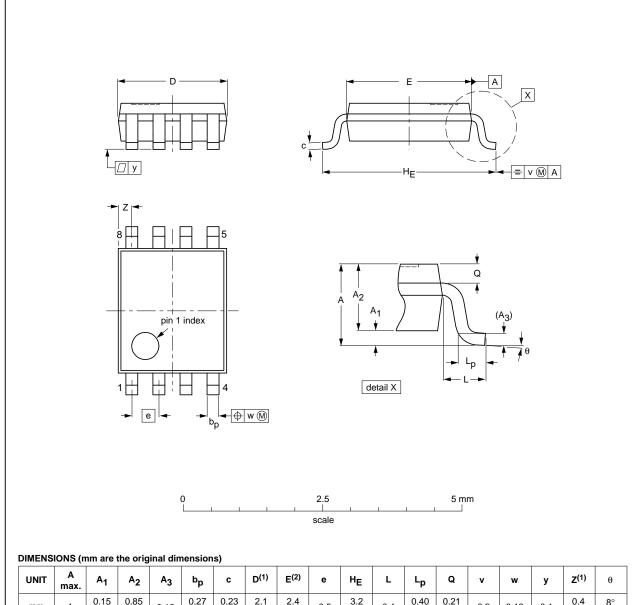
OUTLINE		REFER	EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT505-2					02-01-16

Fig 10. Package outline SOT505-2 (TSSOP8)

74AVC2T45_Q100

VSSOP8: plastic very thin shrink small outline package; 8 leads; body width 2.3 mm

SOT765-1



UNIT	A max.	A ₁	A ₂	A ₃	bp	С	D ⁽¹⁾	E ⁽²⁾	е	HE	L	Lp	ď	v	w	у	Z ⁽¹⁾	θ
mm	1	0.15 0.00	0.85 0.60	0.12	0.27 0.17	0.23 0.08	2.1 1.9	2.4 2.2	0.5	3.2 3.0	0.4	0.40 0.15	0.21 0.19	0.2	0.13	0.1	0.4 0.1	8° 0°

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE	
SOT765-1		MO-187			02-06-07	

Fig 11. Package outline SOT765-1 (VSSOP8)

74AVC2T45_Q100

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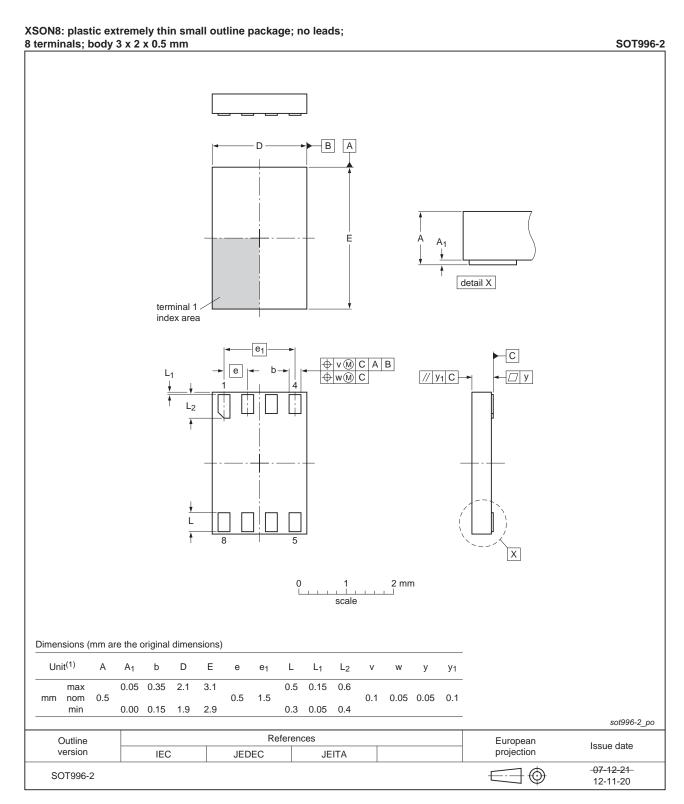


Fig 12. Package outline SOT996-2 (XSON8)

74AVC2T45_Q100

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15. Abbreviations

Table 19. Abbreviations

Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
MIL	Military
MM	Machine Model

16. Revision history

Table 20. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AVC2T45_Q100 v.2	20130215	Product data sheet	-	74AVC2T45_Q100 v.1
Modifications:	 For type number 74AVC2T45GD-Q100 XSON8U has changed to XSON8. 			
74AVC2T45_Q100 v.1	20130131	Product data sheet	-	-

17. Legal information

17.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions"
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